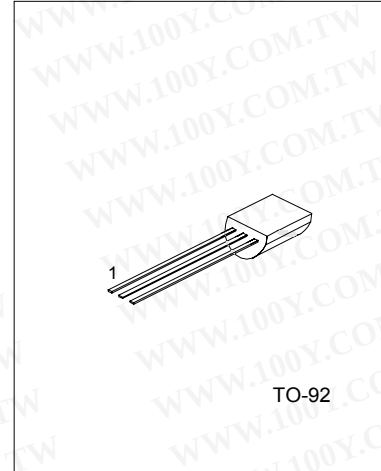


UTC 9015 PNP EPITAXIAL SILICON TRANSISTOR

PRE-AMPLIFIER, LOW LEVEL &
 LOW NOISE

FEATURES

- *High total power dissipation. (450mW)
- *Excellent hFE linearity.
- *Complementary to UTC 9014



1: EMITTER 2: BASE 3: COLLECTOR

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	VCBO	-50	V
Collector-emitter voltage	VCEO	-45	V
Emitter-base voltage	VEBO	-5	V
Collector current	Ic	-100	mA
Collector dissipation	Pc	450	mW
Junction Temperature	Tj	150	°C
Storage Temperature	TSTG	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BVCBO	Ic=-100μA, IE=0	-50			V
Collector-emitter breakdown voltage	BVCEO	Ic=-1mA, IB=0	-45			V
Emitter-base breakdown voltage	BVEBO	IE=-100μA, Ic=0	-5			V
Collector cutoff current	ICBO	VCB=-50V, IE=0			-50	nA
Emitter cutoff current	IEBO	VEB=-5V, Ic=0			-100	nA
DC current gain	hFE	VCE=-5V, Ic=-1mA	60	200	600	
Collector-emitter saturation voltage	VCE(sat)	Ic=-100mA, IB=-5mA		-0.2	-0.7	V
Base-emitter saturation voltage	VBE(sat)	Ic=-100mA, IB=-5mA		-0.82	-1.0	V
Base-emitter on voltage	VBE(on)	VCE=-5V, Ic=-2mA	-0.6	-0.65	-0.75	V
Output Capacitance	Cob	VCB=-10V, IE=0, f=1MHz		4.5	7.0	pF
Current gain-Bandwidth Product	fT	VCE=-5V, Ic=-10mA	100	190		MHz
Noise Figure	NF	VCE=-5V, Ic=-0.2mA f=1KHz, Rs=1KΩ		0.7	10	dB

CLASSIFICATION OF hFE

RANK	A	B	C
RANGE	60-150	100-300	200-600

UTC UNISONIC TECHNOLOGIES CO., LTD.

UTC 9015

PNP EPITAXIAL SILICON TRANSISTOR

